

# SILICON TRANSISTOR 2SC3588-Z

# NPN SILICON TRIPLE DIFFUSED TRANSISTOR MP-3

#### **DESCRIPTION**

2SC3588-Z is designed for High Voltage Switching, especially in Hybrid Integrated Circuits.

#### **FEATURES**

- High Voltage VcEo = 400 V
- Complement to 2SA1400-Z

#### **QUALITY GRADE**

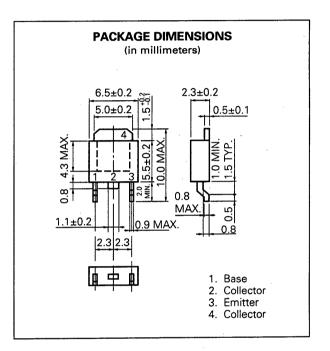
#### Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

#### ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

| Collector to Base Voltage              | Vсво | 500         | ٧  |
|--|------|-------------|----|
| Collector to Emitter Voltage           | VCEO | 400         | ٧  |
| Emitter to Base Voltage                | Vево | 7           | ٧  |
| Collector Current (DC)                 | lc   | 0.5         | Α  |
| Collector Current (Pulse)*             | lc   | 1.0         | Α  |
| Total Power Dissipation (Ta = 25 °C)** | Рт   | 2.0         | W  |
| Junction Temperature                   | Tj   | 150         | °C |
| Storage Temperature                    | Tstg | -55 to +150 | °C |

- PW ≤ 10 ms, Duty Cycle ≤ 50 %
- \*\* When mounted on ceramic substrate of 7.5  $cm^2 \times 0.7$  mm



#### **ELECTRICAL CHARACTERISTICS (Ta = 25 °C)**

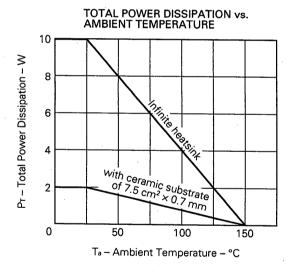
| CHARACTERISTIC               | SYMBOL    | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS  |
|------------------------------|-----------|------|------|------|------|--|
| Collector Cutoff Current     | Ісво      |      |      | 10   | μΑ   | VCB = 400 V, IE = 0  |
| Emitter Cutoff Current       | ІЕВО      |      |      | 10   | μΑ   | VEB = 5.0 V, Ic = 0  |
| DC Current Gain              | hre1*     | 20 - | 42   | 80   |      | VcE = 5.0 V, Ic = 50 mA  |
| DC Current Gain              | hFE2*     | 10   | 20   |      |      | VcE = 5.0 V, lc = 300 mA   |
| Collector Saturation Voltage | VCE(sat)* |      | 0.2  | 0.5  | ٧    | Ic = 300 mA, IB = 60 mA  |
| Base Saturation Voltage      | VBE(sat)* |      | 0.85 | 1.0  | V    | Ic = 300 mA, IB = 60 mA  |
| Turn-on Time                 | ton       |      | 0.12 | 1.0  | μs   | Ic = 0.3 A, RL = 500 Ω   |
| Storage Time                 | tstg      |      | 2.0  | 2.5  | μs   | Vcc = 150 V, PW = 50 μs<br>I <sub>B1</sub> = -I <sub>B2</sub> = 0.06 A<br>Duty Cycle ≦ 2 % |
| Fall Time                    | tf        |      | 0.35 | 1.0  | μs   |  |

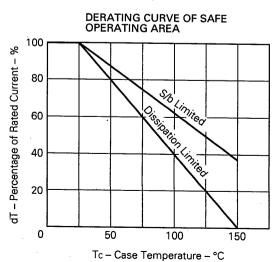
<sup>\*</sup> Pulsed: PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

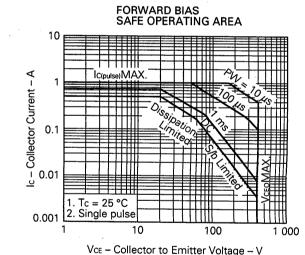
#### **hfe Classification**

| MARKING | М        | L        | К        |
|---------|----------|----------|----------|
| hFE1    | 20 to 40 | 30 to 60 | 40 to 80 |

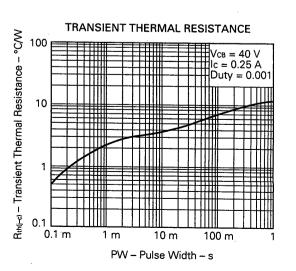
#### TYPICAL CHARACTERISTICS (Ta = 25 °C)

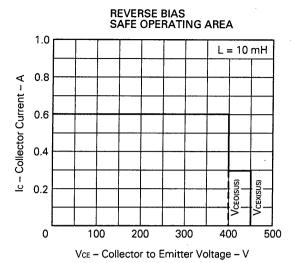




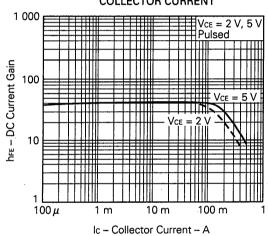




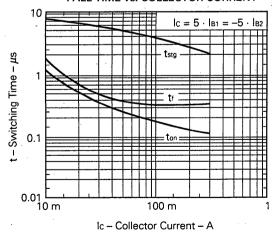




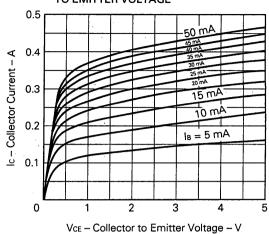




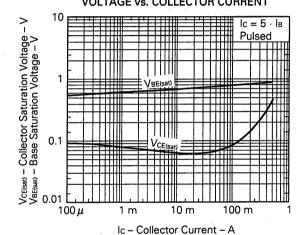
## TURN ON TIME, STORAGE TIME AND FALL TIME vs. COLLECTOR CURRENT



### COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



# BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT





#### Reference

| Application note name  | No.      |
|--|----------|
| Quality control of NEC semiconductors devices.               | TEI-1202 |
| Quality control guide of semiconductors devices.             | MEI-1202 |
| Assembly manual of semiconductors devices.                   | IEI-1207 |
| Design of Push-Pull Type Switching Regulators (Basic)        | TEB-1002 |
| Design of Push-Pull Type Switching Regulators (Applications) | TEB-1003 |
| Optimum Base Drive Conditions of Switching Power Transistors | TEB-1014 |

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Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.

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